Oscillatory magnetotransport between co-propagating quantum Hall edge channels in graphene p-n junctions

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\(^1\)A. F. Young et al., Nat. Phys. 5, 222.
\(^2\)S. Masubuchi, S. Morikawa et al., Jpn J. Appl. Phys. 52, 110105.
\(^3\)S. Morikawa et al., submitted.